Vishay Semiconductors



### Phase Control Thyristors (Hockey PUK Version), 910 A



B-PUK (TO-200AC)

PRIMARY CHARACTERISTICS						
I <sub>T(AV)</sub> 910 A						
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V, 1600 V, 1800 V, 2000 V					
V <sub>TM</sub>	1.80 V					
I <sub>GT</sub>	100 mA					
TJ	-40 °C to +125 °C					
Package	B-PUK (TO-200AC)					
Circuit configuration	Single SCR					

#### FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC)
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS	MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS							
1		910	А							
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C							
		1857	А							
I <sub>T(RMS)</sub>	T <sub>hs</sub>	25	°C							
	50 Hz	15 700	Α							
ITSM	60 Hz	16 400	A							
l <sup>2</sup> t	50 Hz	1232	kA <sup>2</sup> s							
1-1	60 Hz	1125	KA-S							
V <sub>DRM</sub> /V <sub>RRM</sub>		1200 to 2000	V							
t <sub>q</sub>	Typical	150	μs							
TJ		-40 to 125	°C							

VOLTAGE P	VOLTAGE RATINGS									
TYPE NUMBER	CODE V		V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT T <sub>J</sub> = T <sub>J</sub> MAXIMUM mA						
	12	1200	1300							
VS-ST700CL 16		1600	1700	80						
V3-31700CL	18	1800	1900	00						
	20	2000	2100							

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ABSOLUTE MAXIMUM RATING	5						
PARAMETER	SYMBOL		TEST CON	IDITIONS	VALUES	UNITS	
Maximum average on-state current	<b>L</b>	180° condu	ction, half sine	wave	910 (355)	А	
at heatsink temperature	I <sub>T(AV)</sub>	double side	(single side) co	oled	55 (85)	°C	
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink temp	erature double side cooled	1857		
		t = 10 ms	No voltage		15 700		
Maximum peak, one-cycle non-repetitive surge current	<b>L</b>	t = 8.3 ms	reapplied		16 400	A kA <sup>2</sup> s	
	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RBM</sub>		13 200		
		t = 8.3 ms	reapplied	Sinusoidal half wave,	13 800		
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	t = 10 ms	No voltage reapplied 100 % V <sub>RRM</sub>	initial $T_J = T_J$ maximum	1232		
		t = 8.3 ms			1125		
Maximum tion fusing	11	t = 10 ms			871		
		t = 8.3 ms	reapplied		795		
Maximum I <sup>2</sup> $\sqrt{t}$ for fusing	l²√t	t = 0.1 to 10	) ms, no voltage	e reapplied	12 321	kA²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x \ I_{T(AV)} < I < \pi \ x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	1.00	v	
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	), $T_J = T_J maxin$	num	1.13	v	
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x π	(16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			mΩ	
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)})$	0.35	1115.2			
Maximum on-state voltage	V <sub>TM</sub>	$I_{pk} = 2000 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$			1.80	V	
Maximum holding current	I <sub>H</sub>	T 25 °C	anodo supely 1	2 V resistive load	600	mA	
Typical latching current	١ <sub>L</sub>	$1_{\rm J} = 25$ C,	anoue supply 1		1000	ША	

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,t_r \leq 1~\mu s$ $T_J$ = $T_J$ maximum, anode voltage $\leq 80~\%~V_{DRM}$	1000	A/µs				
Typical delay time	t <sub>d</sub>	Gate current 1 A, dl <sub>g</sub> /dt = 1 A/ $\mu$ s V <sub>d</sub> = 0.67 % V <sub>DRM</sub> , T <sub>J</sub> = 25 °C	1.0	110				
Typical turn-off time	tq	$I_{TM}$ = 750 A, $T_J$ = $T_J$ maximum, dl/dt = 60 A/µs, $V_R$ = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ $t_p$ = 500 µs	150	μs				

BLOCKING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/µs			
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	80	mA			



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TRIGGERING							
PARAMETER	SYMBOL	TE	VAL	UNITS			
FARAMETER	STWBOL	I E.	ST CONDITIONS	Тур.	Max.	UNITS	
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum,	$t_p \le 5 ms$	10	0.0	w	
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv	
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \le 5 ms$	3	.0	А	
Maximum peak positive gate voltage	$+V_{GM}$	$T_{J} = T_{J} maximum,$	t < 5 mg	2	20	v	
Maximum peak negative gate voltage	-V <sub>GM</sub>	ij = ij maximum,	5.0		v		
		T <sub>J</sub> = -40 °C		200	-		
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Maximum required gate	100	200	mA	
		T <sub>J</sub> = 125 °C	trigger/ current/voltage are the lowest	50	-		
		$T_J = -40 \ ^\circ C$	value which will trigger all units	2.5	-		
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.8	3.0	V	
		T <sub>J</sub> = 125 °C		1.1	-		
DC gate current not to trigger	I <sub>GD</sub>	T. T	Maximum gate current/voltage not to trigger is the maximum	10		mA	
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J maximum$	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.25		v	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 125	O		
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150			
Moving we there all registerions, investigents besteinly	R <sub>thJ-hs</sub>	DC operation single side cooled	0.073			
Maximum thermal resistance, junction to heatsink		DC operation double side cooled	0.031	к/w		
Maximum thermal resistance, case to heatsink	Р	DC operation single side cooled	0.011	r\/ vv		
Maximum thermal resistance, case to heatsink	R <sub>thC-hs</sub>	DC operation double side cooled	0.006			
Mounting force, ± 10 %			14 700 (1500)	N (kg)		
Approximate weight			255	g		
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-	-200AC)		

CONDUCTION ANGLE	SINUSOIDAL	CONDUCTION	RECTANGULAR	R CONDUCTION	TEOT CONDITIONS			
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS		
180°	0.009	0.009	0.006	0.006				
120°	0.011	0.011	0.011	0.011				
90°	0.014	0.014	0.015	0.015	$T_J = T_J maximum$	K/W		
60°	0.020	0.020	0.021	0.021				
30°	0.036	0.036	0.036	0.036				

Note

• The table above shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC

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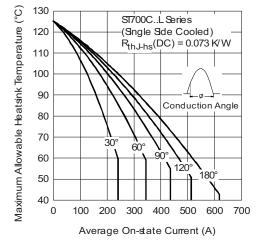


Fig. 1 - Current Ratings Characteristics

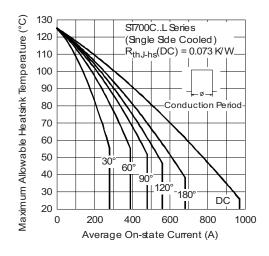


Fig. 2 - Current Ratings Characteristics

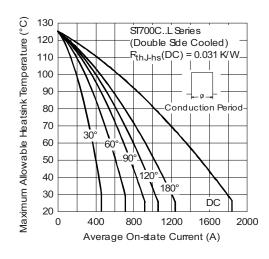


Fig. 3 - Current Ratings Characteristics

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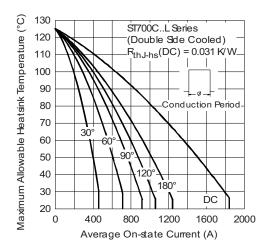


Fig. 4 - Current Ratings Characteristics

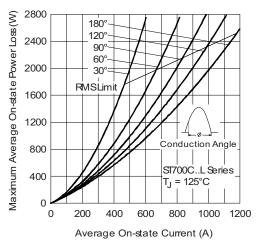
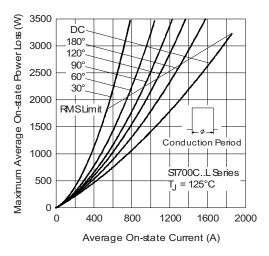


Fig. 5 - On-State Power Loss Characteristics





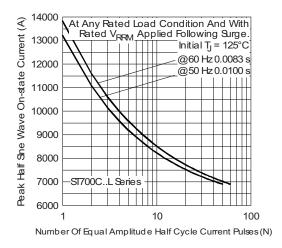
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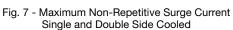
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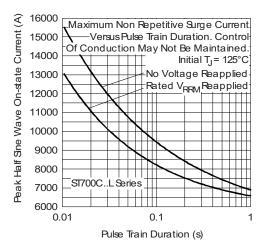
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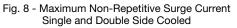
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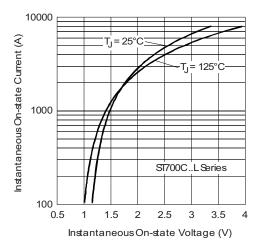
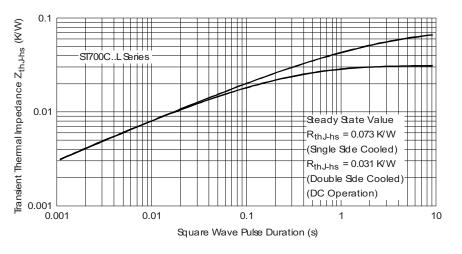
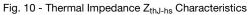


Fig. 9 - On-State Voltage Drop Characteristics





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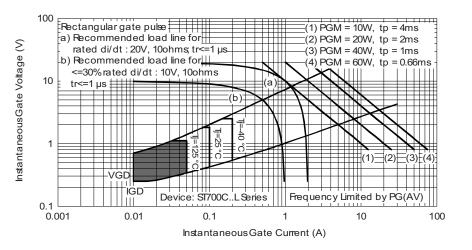


Fig. 11 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

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Device code	VS-	ST	70	0	с	20	L	1	-	
	1	2	3	4	5	6	7	8	9	I
	1 · 2 · 3 ·	- Thy - Ess	ristor ential p	niconduo art numb	ber	oduct				
	4 · 5 · 6 · 7 · 8 ·	- C = - Volt - L =	0 = converter grade C = ceramic PUK Voltage code x 100 = V <sub>RRM</sub> (see Voltage Ratings table) L = PUK case B-PUK (TO-200AC) 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)							
	9	1 = 2 = 3 =	fast-on eyelet t fast-on	terminal erminals terminal dt: • No	ls (gate s (gate a s (gate	and aux and auxi and aux 0 V/µs (	kiliary ca liary ca kiliary ca (standa)	athode u thode so athode s rd selec	unsolde oldered solderec tion)	red leads) leads)

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95076				

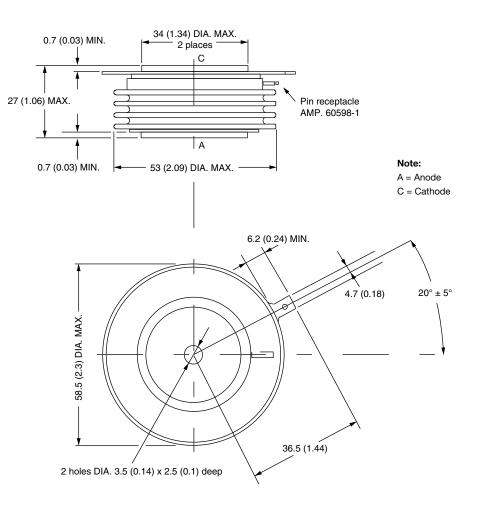
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### **B-PUK (TO-200AC)**

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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